

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	8.5mΩ@10V	24A
	12mΩ@4.5V	



合肥矽普半导体

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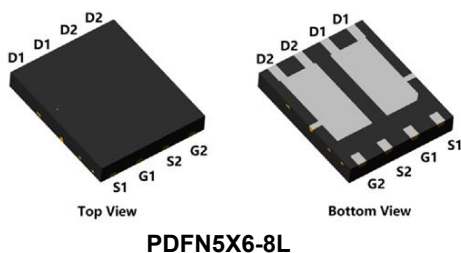
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- **100% UIS TESTED**

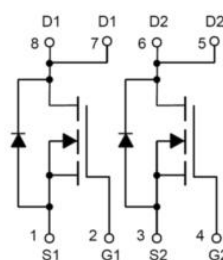
Applications

- Power switching application
- Isolated DC/DC Converters in Telecom and Industrial

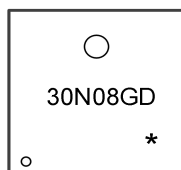
Package



Circuit diagram



Marking



30N08GD :Device Code
* :Month Code

Order Information

Device	Package	Unit/Tape
SP30N08GDNK	PDFN5X6-8L	5000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Tc=25°C)	I _D	24	A
Continuous Drain Current (Tc=100°C)	I _D	16	A
Pulse Drain Current Tested	I _{DM}	96	A
Single Pulse Avalanche Energy ¹	E _{AS}	39.2	mJ
Power Dissipation (Tc=25°C)	P _D	25	W
Power Dissipation (Tc=100°C)	P _D	10	W
Thermal Resistance Junction-to-Case	R _{θJC}	5	°C/W
Maximum Junction Temperature	T _J	-55 to 150	°C
Storage Temperature Range	T _{STG}	-55 to 150	°C

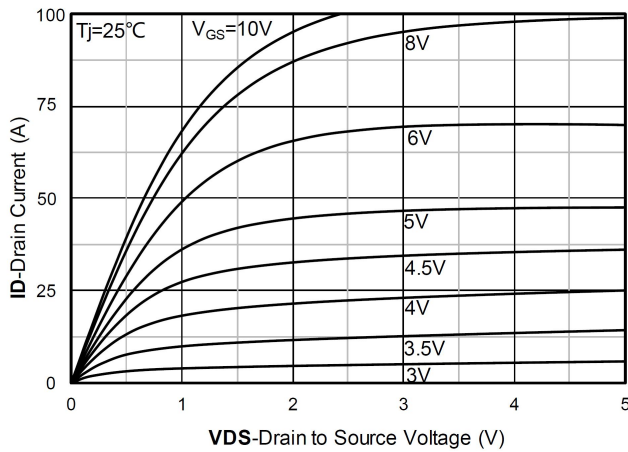
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	VDS=24V , VGS=0V	-	-	1	uA
Gate Leakage Current	I _{GSS}	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	VDS=VGS , ID=250uA	1.3	1.7	2.3	V
Drain-Source On-state Resistance	R _{DS(ON)}	VGS=10V , ID=15A	-	8.5	11	mΩ
		VGS=4.5V , ID=10A	-	12	16	
Gate Resistance	R _G	f=1MHz	-	1.5	-	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	VDS=15V , VGS=0V , f=1MHz	-	625	-	pF
Output Capacitance	C _{oss}		-	240	-	
Reverse Transfer Capacitance	C _{rss}		-	25	-	
Total Gate Charge	Q _g	VDS=15V , VGS=10V , ID=10A	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	3	-	
Gate-Drain Charge	Q _{gd}		-	2	-	
Gate Plateau Voltage	V _{plateau}		-	3.4	-	V
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	VGS=10V , VDD=15V , ID=12A , RG=2Ω	-	7	-	nS
Rise Time	t _r		-	18.8	-	
Turn-Off Delay Time	t _{d(off)}		-	19.5	-	
Fall Time	t _f		-	3.4	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	I _S		-	-	24	A
Reverse Recovery Time	T _{rr}	IS=10A , di/dt=100A/μs , TJ=25℃	-	11	-	nS
Reverse Recovery Charge	Q _{rr}		-	18	-	nC

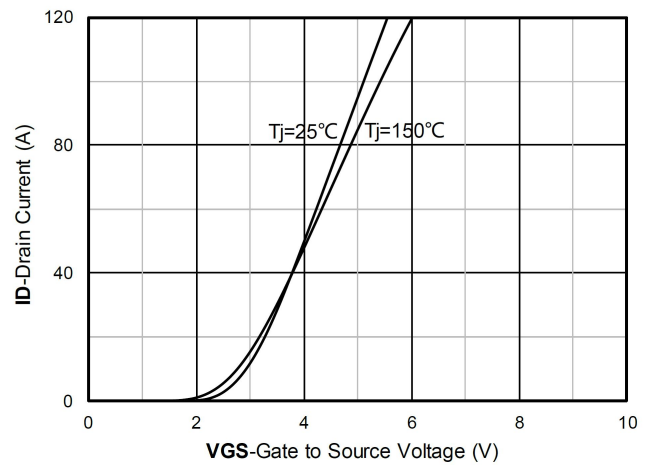
Note :

1. The test condition is VDD=15V, VGS=10V, L=0.5mH, RG=25Ω;

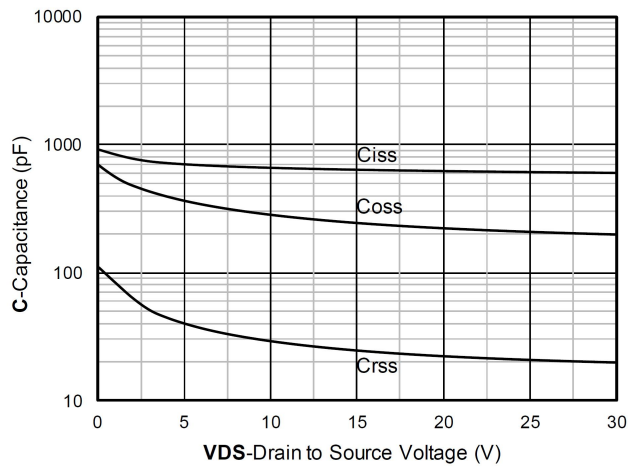
Typical Characteristics



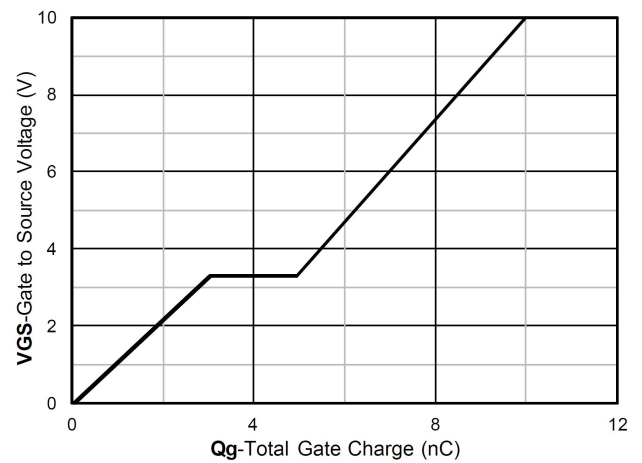
Output Characteristics



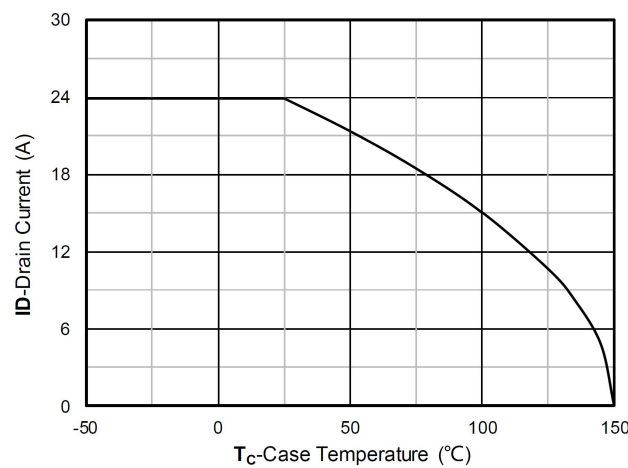
Transfer Characteristics



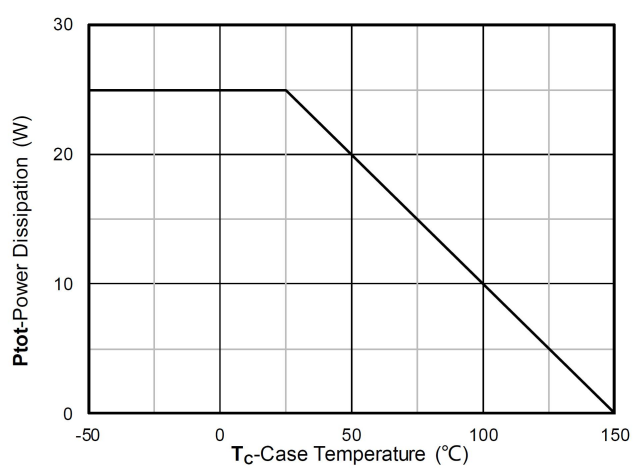
Capacitance Characteristics



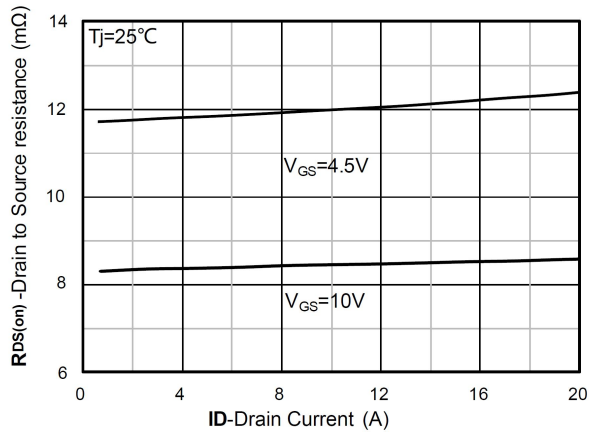
Gate Charge



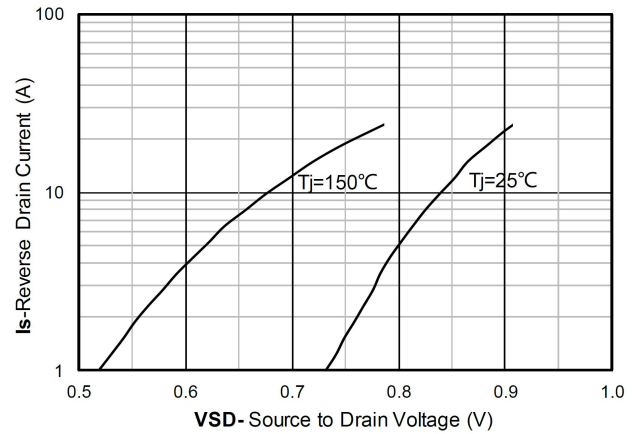
Current dissipation



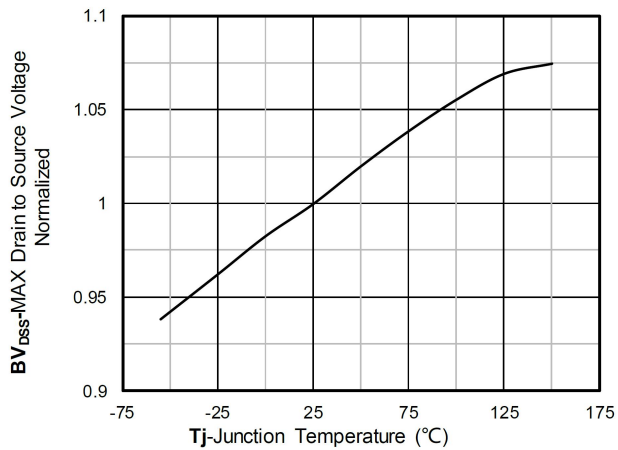
Power dissipation



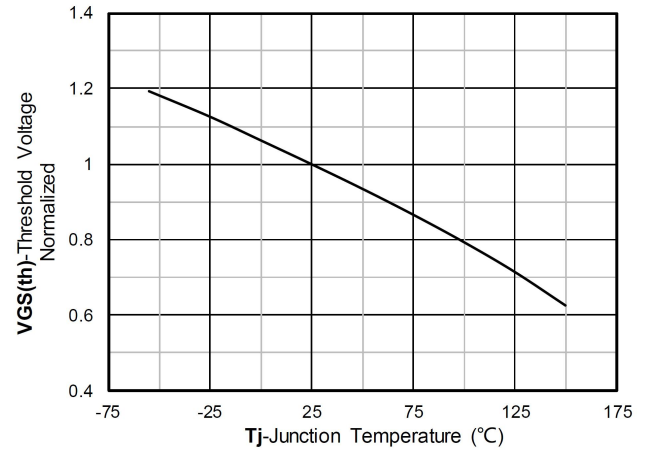
RDS(on) vs. Drain Current



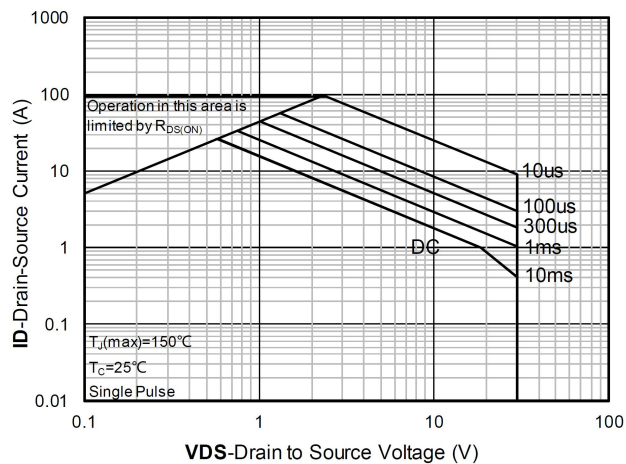
Forward characteristics of reverse diode



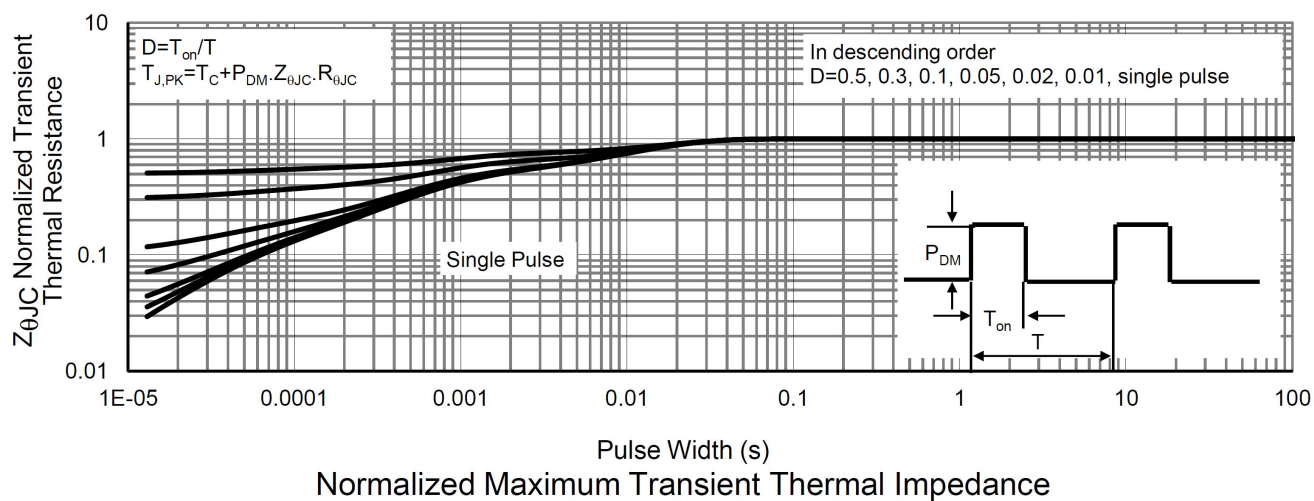
Normalized breakdown voltage



Normalized Threshold voltage

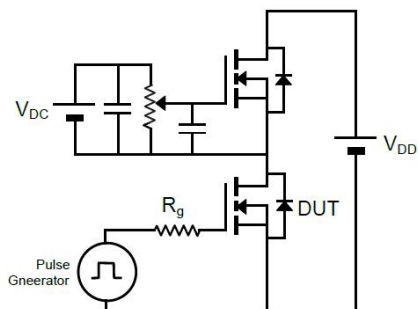
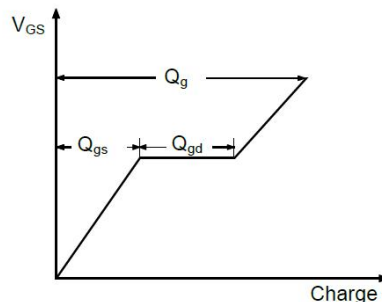


Safe Operation Area

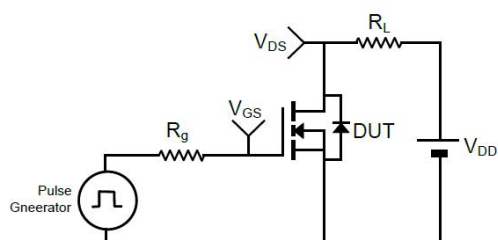
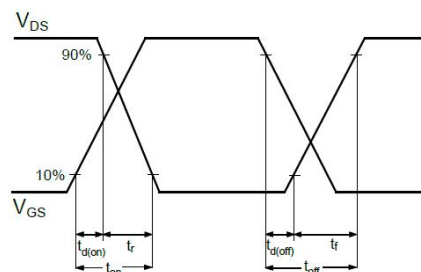


Test Circuit

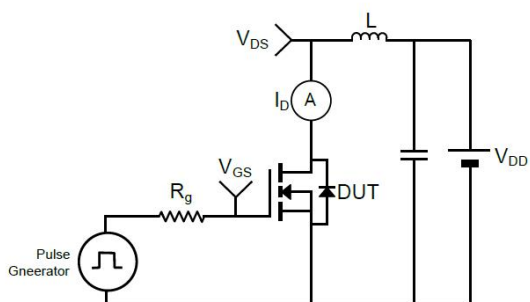
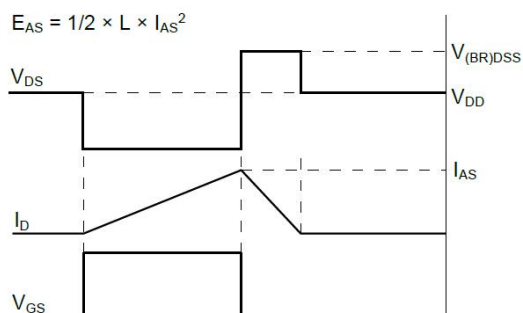
Gate Charge



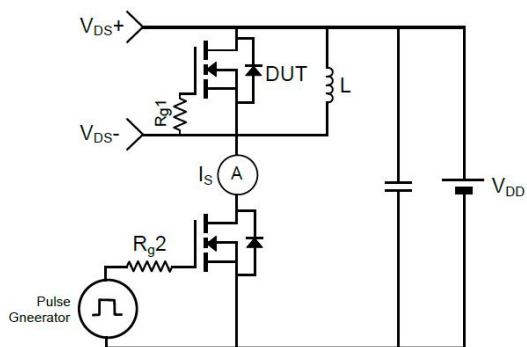
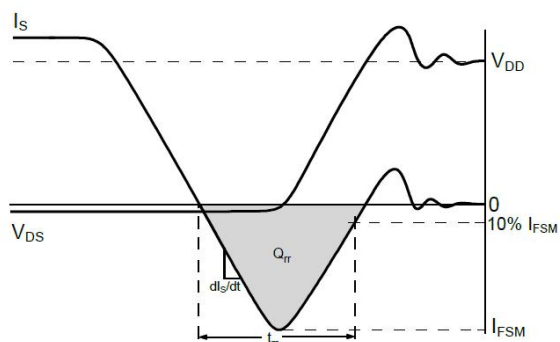
Resistive Load Switching Time



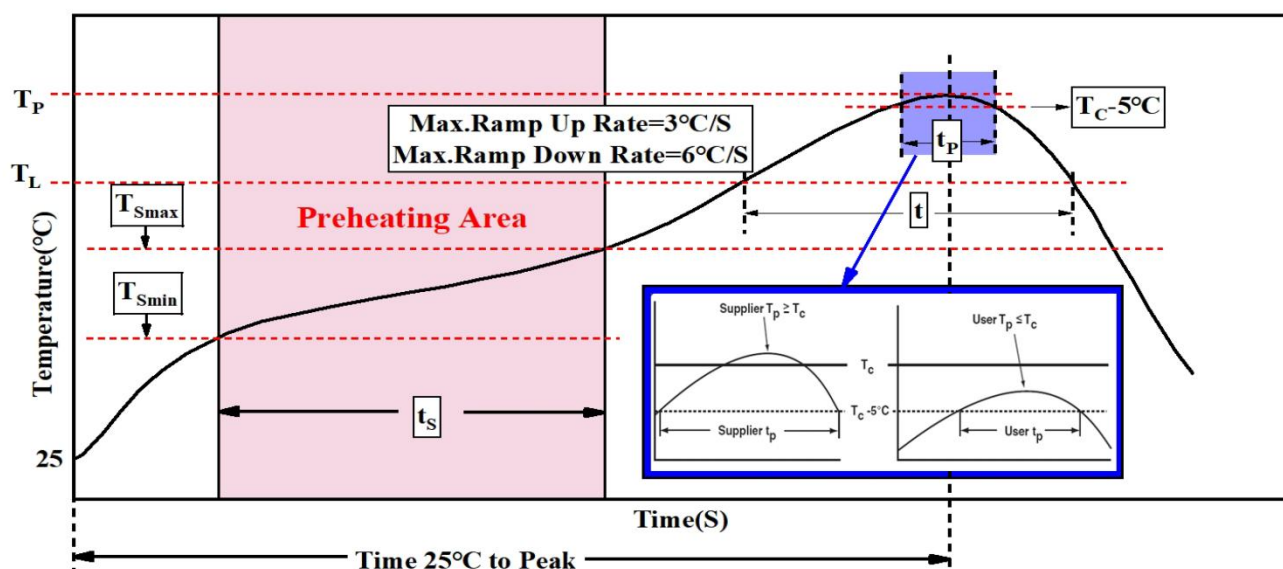
Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{Smin})	100°C	150°C
Temperature max (T_{Smax})	150°C	200°C
Time (T_{Smin} to T_{Smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{Smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217°C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T_P)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_C)	20** seconds	30** seconds
Average ramp-down rate (T_P to T_{Smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_P) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_P) is defined as a supplier minimum and a user maximum		

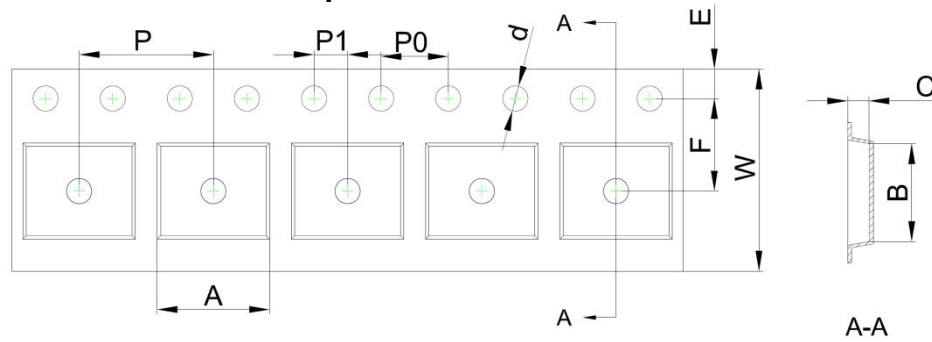
Table 1. SnPb Eutectic Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

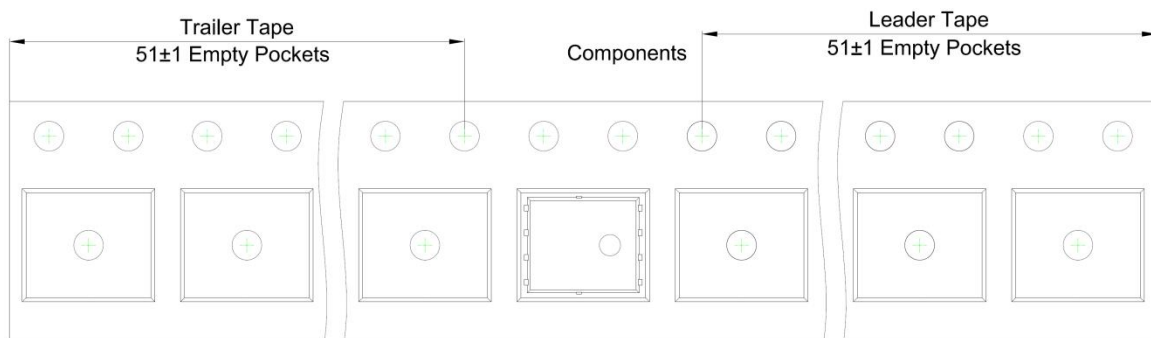
PDFN5X6-8L Embossed Carrier Tape



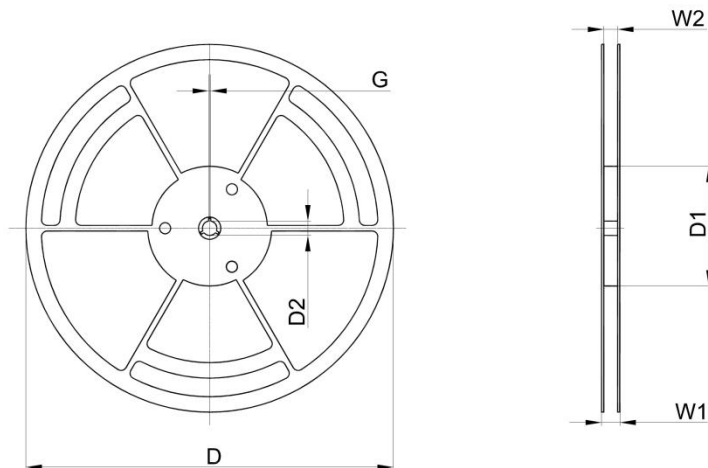
Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFN5X6-8L	6.30	5.30	1.10	Φ1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5X6-8L Tape Leader and Trailer



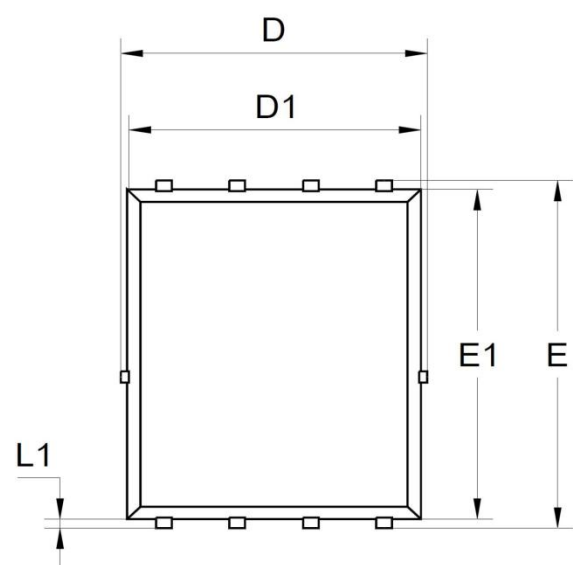
PDFN5X6-8L Reel



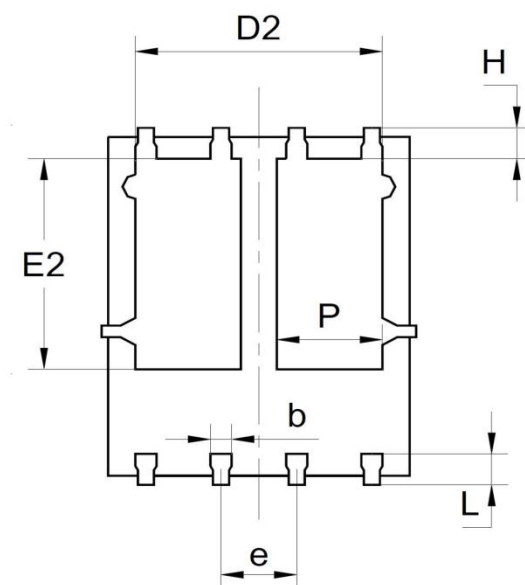
Dimensions are in millimeter

Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

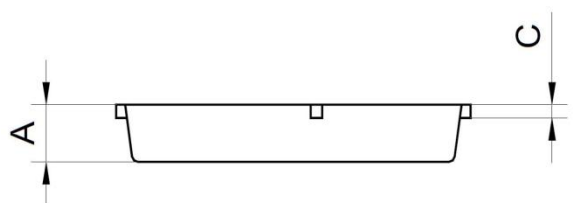
REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365

PDFN5X6-8L Package Information


Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.120	0.035	0.044
b	0.330	0.510	0.013	0.020
C	0.110	0.340	0.004	0.013
D	4.700	5.260	0.185	0.207
D1	4.700	5.100	0.185	0.201
D2	3.560	4.500	0.140	0.177
E	5.750	6.250	0.226	0.246
E1	5.600	6.000	0.220	0.236
E2	3.180	3.660	0.125	0.144
e	1.170	1.370	0.046	0.054
L	0.350	0.710	0.014	0.028
L1	0.060	0.200	0.002	0.008
H	0.350	0.710	0.014	0.028
P	1.700	2.300	0.067	0.091